	Hits	Search Text	DBs
15	170	((first near5 (photoresist or resist or photosensitive) near9 (layer or material or coat$3 or deposit$3 or film or form$3) near22 (expos$4 or illuminat$4 or irradiat$4) near35 (mask or reticle or photomask or phase$4shift$4mask or (alternat$5 near6 shift$5 near8 ($4mask or reticle))) near29 develop$4) same (strip$4 or remov$4 or wash$4) same (((hard near5 mask) or metal$4 or conductive or insulat$4 or dielectric) near9 pattern))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
16	486	(((deposit$4 or coat$4 or form$4 or apply$4) near22 (conductive or metal$4 or insulat$4 or dielectric or Ni or Cu)) same (second near8 (photoresist or resist or photosensitive) near12 (layer or form$3 or film or deposit$4 or coat$4) near22 (expos$4 or irradiat$4 or illuminat$4) near36 (trim$4 or (reduc$5 near9 (size or width)) or etch$4) near26 develop$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
17	49	S15 and S16	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
18	264	((deposit$4 or coat$4 or form$4 or apply$4) near22 (conductive or (hard near9 mask) or metal$4 or insulat$4 or dielectric or Ni or Cu or material) near16 (pattern$4 or (lithograph$4 near9 pattern$4))) and (second near8 (photoresist or resist) near12 (layer or form$3 or film or deposit$4 or coat$4) near22 (expos$4 or irradiat$4 or illuminat$4) near36 (trim$4 or (reduc$5 near9 (size or width)) or etch$4) near19 (second near9 (photomask or mask or reticle)) near26 develop$4)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
19	16	430/311.ccls. and (((deposit$4 or coat$4 or form$4 or apply$4) near22 (conductive or metal$4 or insulat$4 or dielectric or Ni or Cu)) same (second near8 (photoresist or resist) near12 (layer or form$3 or film or deposit$4 or coat$4) near22 (expos$4 or irradiat$4 or illuminat$4) near36 (trim$4 or (reduc$5 near9 (size or width)) or etch$4) near26 develop$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
20	588	(first near5 (photoresist or resist or photosensitive) near9 (layer or material or coat$3 or deposit$3 or film or form$3) near22 (expos$4 or illuminat$4 or irradiat$4) near35 (mask or reticle or photomask) near29 develop$4 near30 (strip$4 or remov$4 or wash$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
21	79	S20 and S21	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
22	28	S20 and S21	US-PGPUB
23	21	430/313.ccls. and (((deposit$4 or coat$4 or form$4 or apply$4) near22 (conductive or metal$4 or insulat$4 or dielectric or Ni or Cu)) same (second near8 (photoresist or resist) near12 (layer or form$3 or film or deposit$4 or coat$4) near22 (expos$4 or irradiat$4 or illuminat$4) near36 (trim$4 or (reduc$5 near9 (size or width)) or etch$4) near26 develop$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB
24	8	430/394.ccls. and (((deposit$4 or coat$4 or form$4 or apply$4) near22 (conductive or metal$4 or insulat$4 or dielectric or Ni or Cu)) same (second near8 (photoresist or resist) near12 (layer or form$3 or film or deposit$4 or coat$4) near22 (expos$4 or irradiat$4 or illuminat$4) near36 (trim$4 or (reduc$5 near9 (size or width)) or etch$4) near26 develop$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
25	14	430/316.ccls. and (((deposit$4 or coat$4 or form$4 or apply$4) near22 (conductive or metal$4 or insulat$4 or dielectric or Ni or Cu)) same (second near8 (photoresist or resist) near12 (layer or form$3 or film or deposit$4 or coat$4) near22 (expos$4 or irradiat$4 or illuminat$4) near36 (trim$4 or (reduc$5 near9 (size or width)) or etch$4) near26 develop$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB